Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4	"039484".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/25 08:53
L2	2109	((703/13) or (703/14) or (257/48)).CCLS.	US-PGPUB; USPAT	OR	OFF	2004/11/25 08:54
L3	16	2 and calibrat$3 near2 (device structure transistor circuit IC ULSI vlsi) and test$3 near2 (device structure transistor circuit IC ULSI vlsi)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/25 08:57
L4	12	2 and calibrat$3 near2 (device structure transistor circuit IC ULSI vlsi) and test$3 near2 (device structure transistor circuit IC ULSI vlsi) and design$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/25 08:56
S1	5	"039404".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/25 08:48
S2	4	"039484".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/07 12:04
S3	28	method near4 circuit adj simulation.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/07 12:08
S4	0	apparatus near6 computer adj simulation near6 circuit.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/07 12:09
S5	162	computer adj system near6 simulation.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/07 12:10
S6	8	(US-20030154064-$ or US-20030154065-$ or US-20030154447-$ or US-20030154453-$ or US-20030154454-$ or US-20030163277-$ or US-20030163510-$ or US-20030164239-$).did.	US-PGPUB	OR	OFF	2003/09/07 12:42

S7	0	"simulating.clm" and apparatus.clm. and design.clm.	US-PGPUB; USPAT	OR	OFF	2003/09/07 12:43
S8	840	simulating near6 circuit.clm.	US-PGPUB; USPAT	OR	OFF	2003/09/07 12:44
S9	7	(US-20030154453-$ or US-20030154454-$ or US-20030163277-$ or US-20030163510-$ or US-20030154447-$ or US-20030154065-$ or US-20030154064-$).did.	US-PGPUB	OR	OFF	2004/05/19 11:21
S10	1136	((703/13) or (703/14)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/11/25 08:49
S11	42	(((703/13) or (703/14)).CCLS.) and method near6 capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/19 14:16
S12	0	(((703/13) or (703/14)).CCLS.) and method near6 capacitance and simulat$3 near6 design adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/19 14:21
S13	0	method near6 capacitance near6 simulat$3 and simul$3 near6 design adj structure and parasitic adj capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/19 15:16
S14	0	method near6 capacitance near6 simulat$3 and simul$3 near6 design adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/19 15:16
S15	1814	circuit near3 simulat$3.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/19 15:16
S16	95	circuit near3 simulat$3.clm. and method near6 (capacitance capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/19 15:35
S17	34	circuit near3 simulat$3.clm. and method near6 (capacitance capacitor) and design near6 simulat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/19 17:26

S18	15	gallia.in. near6 james.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/19 17:29
S19	5	gallia.in. near6 james.in. and design$3 and capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/19 17:31
S20	19	(design$3 determin$3) near3 capacitance near20 (circuit near2 simulat$3).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/19 17:33
S21	7	(design$3 determin$3) near3 capacitance near20 (circuit near2 simulat$3).ti,ab,clm. and parasitic. ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/20 10:38
S22	1137	((703/13) or (703/14)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 10:38
S23	58	(((703/13) or (703/14)).CCLS.) and circuit adj simulati$2 and design and capacitance and parasitic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 10:51
S24	0	(((703/13) or (703/14)).CCLS.) and circuit adj simulati$2 and design adj structure and test adj structure and capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 10:52
S25	0	(((703/13) or (703/14)).CCLS.) and circuit adj simulati$2 and design adj structure and test adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 10:52
S26	158	(((703/13) or (703/14)).CCLS.) and circuit adj simulati$2 and design and test	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 10:52
S27	8	(((703/13) or (703/14)).CCLS.) and circuit adj simulati$2 and design and test and capacitance and parasitic adj capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 11:10

S28	4	(((703/13) or (703/14)).CCLS.) and circuit adj simulati$2 and design and test and capacitance and (wire interconnect) adj capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 11:18
S29	0	estimat$3 near2 parasitic adj capacitance near8 test	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 11:19
S30	37	estimat$3 near2 parasitic adj capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 11:19
S31	1	estimat$3 near2 parasitic adj capacitance and test adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 11:20
S32	0	estimat$3 near2 parasitic adj capacitance and test adj (device transistor capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 11:22
S33	12	estimat$3 near2 parasitic adj capacitance and simulation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 14:10
S34	2	("6243653").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 15:35
S35	6	extraction near4 parasitic adj capacitance.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 15:36
S36	4	extraction near4 parasitic adj capacitance.ti,ab,clm. and circuit near2 simulat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/20 15:36
S37	0	"6243653".pn. and physical$2 near3 test$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/21 10:40

S38	0	"6243653".pn. and test$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/21 10:40
S39	0	(("6243653").PN.) and physical$2 and test$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/21 10:41
S40	0	(("6243653").PN.) and test$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/21 10:41
S41	2	("6243653").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/21 10:42
S42	0	physical$2 near2 test$3 and extract$3 near3 parasitic adj capaciance and simulat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/21 10:43
S43	1	physical$2 near2 test$3 and extract$3 near3 parasitic adj capacitance and simulat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/21 10:53
S44	2	("5706206").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/21 11:10
S45	6	capacitance near3 test$3 and capacitance near3 design$3 and parasitic adj capacitance near4 test$3 near6 design$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/21 11:12
S46	6	capacitance near3 (physical test$3) and capacitance near3 (simulat$3 design$3) and parasitic adj capacitance near4 test$3 near6 design$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/21 11:13
S47	45	capacitance near3 (physical test$3) and capacitance near3 (simulat$3 design$3) and parasitic adj capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/21 11:13

S48	56	(extracting extraction) near4 (parasitic adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/24 19:39
S49	5	(extracting extraction) near4 (parasitic adj capacitance) and subtract$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/24 19:48
S50	2	(extracting extraction) near4 (parasitic adj capacitance) and subtract$3 and sum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/24 19:56
S51	5	(extracting extraction) near4 (parasitic adj capacitance) and subtract$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/24 19:56
S52	6	raphael and parasitic adj capacitance and three adj dimensional	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/25 14:34
S53	126	cmos and gate adj contact and parasitic adj capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/25 14:35
S54	84	width near2 gate and parasitic adj capacitance and (extracting extraction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/26 10:42
S55	2	width near2 gate and parasitic adj capacitance near3 (extracting extraction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/26 12:57
S56	0	raphael.ti,ab,clm. and boundary adj conditions	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/26 12:57
S57	3	raphael and boundary adj conditions and parasitic adj capacitance.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/26 12:57

S58	2	overlap near3 gate and parasitic adj capacitance and raphael	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/27 13:17
S59	3473	capacitance near3 drain near4 source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/27 16:40
S60	108	capacitance near3 drain near4 source and parasitic adj capacitance and simulation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/27 16:41
S61	102	capacitance near3 drain near3 source and parasitic adj capacitance and simulation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/27 17:28
S62	1	calibration adj structure and parasitic adj capacitance and test adj structure and simulation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/27 17:29
S63	2	calibration and parasitic adj capacitance and test adj structure and simulation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/27 17:31
S64	2	calibrati$2 and parasitic adj capacitance and test adj structure and simulation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/27 17:31
S65	2	"6449754".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/28 09:12
S66	19722	apparatus near3 simulating near3 integrated circuit near3 operation. clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/28 15:18
S67	0	apparatus near3 simulating near3 integrated adj circuit near3 operation.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/28 15:18

S68	0	apparatus near6 simulating near6 integrated adj circuit near6 operation.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/28 15:22
S69	0	apparatus near6 simulating near6 integrated adj circuit near6 operation.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/28 15:23
S70	1	apparatus near6 simulati$2 near6 integrated adj circuit near6 operation.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/28 15:24
S71	4964	apparatus near6 simulati$2.ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/28 15:24
S72	4087	apparatus near3 simulati$2.ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/28 15:25
S73	383	apparatus near3 simulati$2 near6 (semiconductor integrated circuit). ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/28 15:26
S74	4	"039484".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/28 19:16
S75	2	("6169302").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/29 18:06
S76	62	apparatus near3 simulating near3 circuit.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/29 18:06
S77	7	apparatus near3 simulating near3 circuit.ti,ab,clm. and computer.ti,ab, clm. and processor.ti,ab,clm. and memory.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/29 18:07